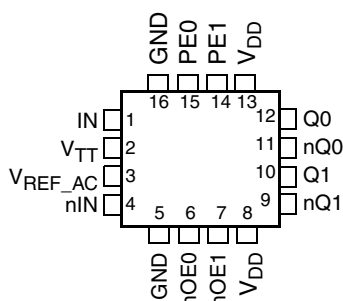


General Description

The ICS854S712I is a differential, high-speed 1:2 data/clock fanout buffer and line driver. The outputs support pre-emphasis in order to drive backplanes and long transmission lines while reducing inter-symbol interference effects. The pre-emphasis level is configurable to optimize for low bit error rate or power consumption. Pre-emphasis utilizes an increased output voltage swing for transition bits. The device is optimized for data rates up to 4.5 Gbps (NRZ) and for deterministic jitter in data applications and low additive jitter in clock applications. The outputs are LVDS-compliant while the differential input is compatible with a variety of signal levels such as LVDS, LVPECL and CML. Internal input termination, a bias voltage output for AC-coupling and small packaging (VFQFN) supports space-efficient board designs. The ICS854S712I operates from a 3.3V power supply and supports the industrial temperature range of -40°C to +85°C.

Pin Assignment



ICS854S712I
16 lead VFQFN
3.0mm x 3.0mm x 0.925mm
package body
K Package
Top View

Features

- 1:2 differential data/clock fanout buffer and line driver
- 4.5 Gbps data rate (NRZ) (maximum)
- Differential LVDS outputs
- Differential input supporting LVDS, LVPECL and CML levels
- Configurable output pre-emphasis
- Low-skew outputs: 10ps (maximum)
- Low data deterministic jitter: 4ps (maximum)
- LVCMOS interface levels for the control inputs
- Asynchronous output disable into high-impedance state
- Internal input termination: 100Ω (Differential)
- Additive phase jitter, RMS: 0.08ps (typical)
- Full 3.3V supply voltage
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Block Diagram

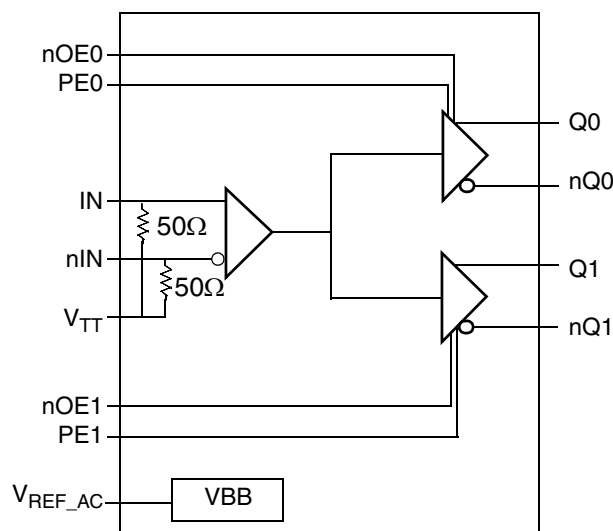


Table 1. Pin Descriptions

Number	Name	Type		Description
1	IN	Input		Non-inverting differential data and clock input. LVDS, LVPECL or CML interface levels. 50Ω to V_{TT} .
4	nIN	Input		Inverting differential data and clock input. LVDS, LVPECL or CML interface levels. 50Ω to V_{TT} .
6, 7	nOE0, nOE1	Input	Pulldown	Output enable control. LVCMOS/LVTTL interface levels.
15, 14	PE0, PE1	Input	Pulldown	Pre-emphasis control. LVCMOS/LVTTL interface levels.
12, 11	Q0, nQ0	Output		Differential output pair. LVDS interface levels.
10, 9	Q1, nQ1	Output		Differential output pair. LVDS interface levels.
3	V_{REF_AC}	Output		Bias voltage reference for AC-coupling.
2	V_{TT}			Center tap for input termination. Leave floating for LVDS input, connect to 50Ω to GND for LVPECL inputs and to the V_{REF_AC} output for AC-coupled applications.
5, 16	GND	Power		Power supply ground.
8, 13	V_{DD}	Power		Power supply pins.

NOTE: *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C_{IN}	Input Capacitance			2		pF
$R_{PULLDOWN}$	Input Pulldown Resistor			51		$k\Omega$

Device Configuration

Table 3A. Output Enable Control

Inputs		Outputs	
nOE1	nOE0	Q1, nQ1	Q0, nQ0
0 (default)	0 (default)	Enabled	Enabled
0	1	Enabled	Disabled (Logic 0)
1	0	Disabled (Logic 0)	Enabled
1	1	Disabled (Logic 0)	Disabled (Logic 0)

NOTE: nOEx are asynchronous controls.

Table 3B. Output Pre-Emphasis Control

Input		Pre-Emphasis	
PE1	PE0	Q1, nQ1	Q0, nQ0
0 (default)	0 (default)	Off	Off
0	1	Off	On
1	0	On	Off
1	1	On	On

NOTE: PEx are asynchronous controls.

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to $V_{DD} + 0.5V$
Outputs, I_O Continuous Current Surge Current	10mA 15mA
I_{IN} , Input Current, I_N , nIN	$\pm 50mA$
V_{TT} , Current, I_{VT}	$\pm 100mA$
V_{REF_AC} , Input Sink/Source Current, I_{REF_AC}	$\pm 2mA$
Package Thermal Impedance, θ_{JA}	74.7°C (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Power Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current				90	mA

Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^\circ C$ to $85^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage		2.2		$V_{DD} + 0.3$	V
V_{IL}	Input Low Voltage		-0.3		0.8	V
I_{IH}	Input High Current	PE0, PE1, nOE0, nOE1 $V_{DD} = V_{IN} = 3.465V$			150	μA
I_{IL}	Input Low Current	PE0, PE1, nOE0, nOE1 $V_{DD} = 3.465V, V_{IN} = 0V$	10			μA

Table 4C. DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
R_{IN}	Input Resistance	IN, nIN	IN to V_{TT}	40	50	60	Ω
V_{IH}	Input High Voltage	IN, nIN		1.2		V_{DD}	V
V_{IL}	Input Low Voltage	IN, nIN		0		$V_{IH} - 0.15$	V
V_{IN}	Input Voltage Swing; NOTE 1			0.15		1.2	V
V_{DIFF_IN}	Differential Input Voltage Swing			0.3		2.4	V
V_{REF_AC}	Bias voltage reference			$V_{DD} - 1.35$	$V_{DD} - 1.30$	$V_{DD} - 1.25$	V
I_{IN}	Input Current; NOTE 2	IN, nIN				35	mA

NOTE 1: Refer to Parameter Measurement Information, Input Voltage Swing Diagram.

NOTE 2: Guaranteed by design.

Table 4D. LVDS DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OD}	Differential Output Voltage	Pre-Emphasis off (PE0=PE1=0)	300	450	650	mV
ΔV_{OD}	V_{OD} Magnitude Change	Pre-Emphasis off (PE0=PE1=0)			50	mV
V_{OS}	Offset Voltage	Pre-Emphasis off (PE0=PE1=0)	1.10	1.25	1.40	V
ΔV_{OS}	V_{OS} Magnitude Change	Pre-Emphasis off (PE0=PE1=0)			50	mV

AC Electrical Characteristics

Table 5. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $T_A = -40^{\circ}C$ to $+85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{REF}	Input Reference Frequency		Alternating 01 pattern (Clock)			3.0	GHz
f_{OUT}	Output Frequency		Alternating 01 pattern (Clock)			3.0	GHz
	Operating Data Rate		NRZ (PRBS 2^7-1 Pattern)			4.5	Gbps
t_{PD}	Propagation Delay; NOTE 1		Alternating 01 pattern (Clock)	300		500	ps
$t_{sk(p)}$	Output Pulse Skew		Alternating 01 pattern (Clock)			20	ps
$t_{sk(o)}$	Output Skew, NOTE 2, 4		Alternating 01 pattern (Clock)			10	ps
$t_{sk(pp)}$	Part-to-Part Skew: NOTE 3, 4		Alternating 01 pattern (Clock)			150	ps
t_{EN}	Output Enable Time: NOTE 5					1.25	ns
t_{DIS}	Output Disable Time: NOTE 5					1.35	ns
V_{PE}	Output Pre-Emphasis Voltage Ratio; NOTE 5		$f_{OUT} = 300MHz$, Pre-Emphasis Off		0		dB
			$f_{OUT} = 300MHz$, Pre-Emphasis On		2		dB
Δt_{PE}	Output Pre-Emphasis Duration; NOTE 5		$f_{OUT} = 300MHz$, Pre-Emphasis On		300		ps
σ_{jit}	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter section		Alternating 01 pattern (Clock), 491.52MHz, Integration Range: 12kHz - 20MHz		0.08		ps
t_{DJ}	Deterministic Jitter Peak-Peak; NOTE 5, 6		K28.5 Pattern, 1.5 Gbps, Pre-Emphasis On			4	ps
t_{TJ}	Total Jitter Peak-Peak; NOTE 5		NRZ (PRBS 2^7-1 Pattern), 1.5 Gbps, Pre-Emphasis On			4	ps
t_R / t_F	Output Rise/ Fall Time	$f_{OUT} \leq 625MHz$	20% to 80%, 491.52MHz Alternating 01 pattern (Clock)	50		400	ps
		$f_{OUT} = 1.25GHz$		65		200	ps
		$f_{OUT} = 2.25GHz$		80		100	ps

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: All parameters characterized at $f_{OUT} \leq 1.25GHz$ and pre-emphasis off, unless otherwise noted.

NOTE 1: Measured from the differential input crossing point to the differential output crossing point.

NOTE 2: Defined as skew between outputs at the same supply voltages and with equal load conditions. Measured at the output differential cross points.

NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltage, same temperature, same frequency and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

NOTE 4: This parameter is defined according with JEDEC Standard 65.

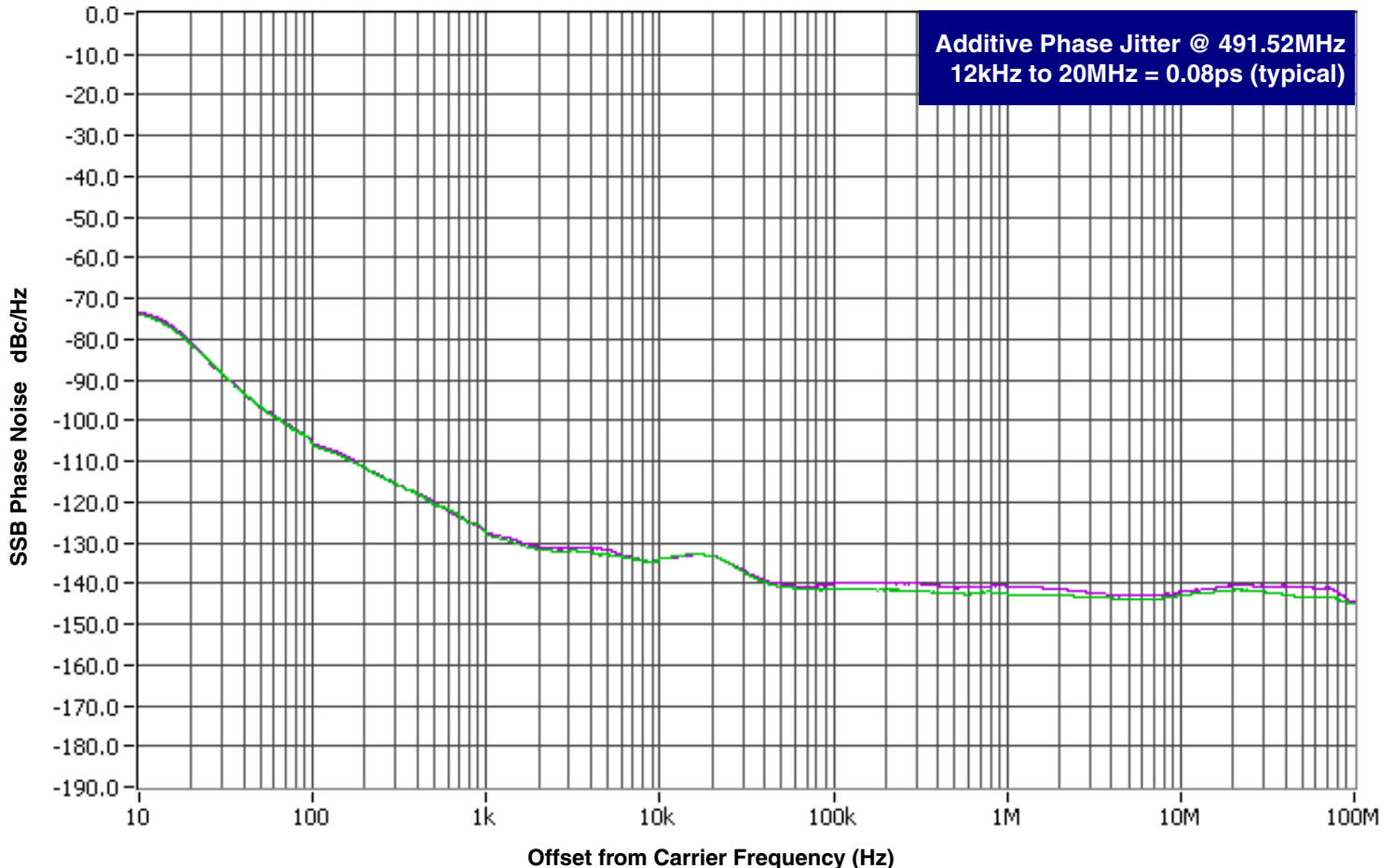
NOTE 5: These parameters are guaranteed by characterization.

NOTE 6: A repeating K28.5 sequence (composed of alternating K28.5+ and K28.5-) contains the symbols 0011111010 1100000101. This pattern contains five consecutive 1's and five consecutive 0's, (the longest consecutive identical digits found in 8B/10B coded data)

Additive Phase Jitter

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the ***dBc Phase Noise***. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio

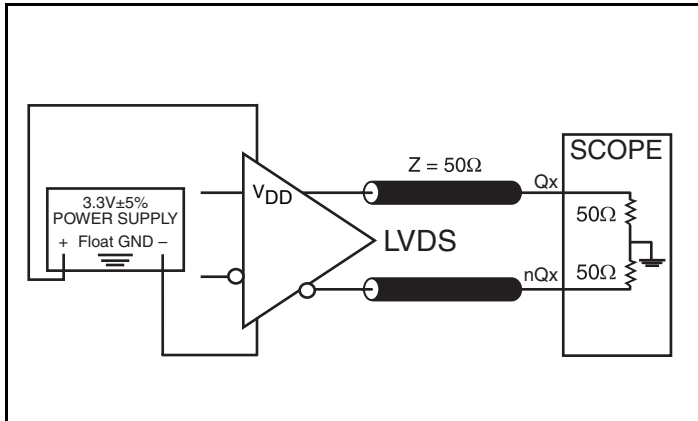
of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a ***dBc*** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



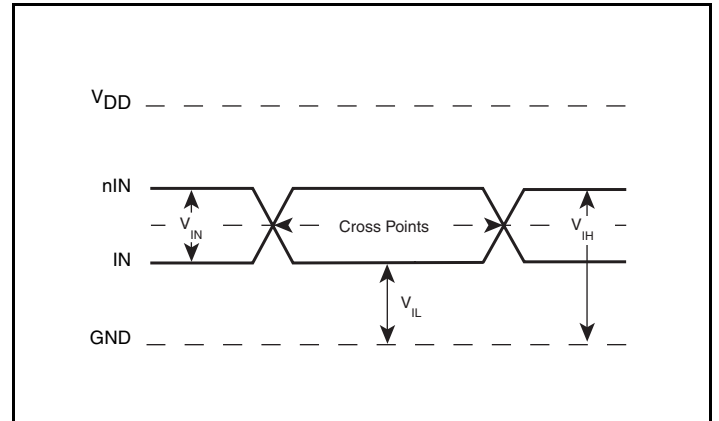
As with most timing specifications, phase noise measurements have issues relating to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

The source generator "IFR2042 10kHz – 6.4GHz Low Noise Signal Generator as external input to an Agilent 8133A 3GHz Pulse Generator".

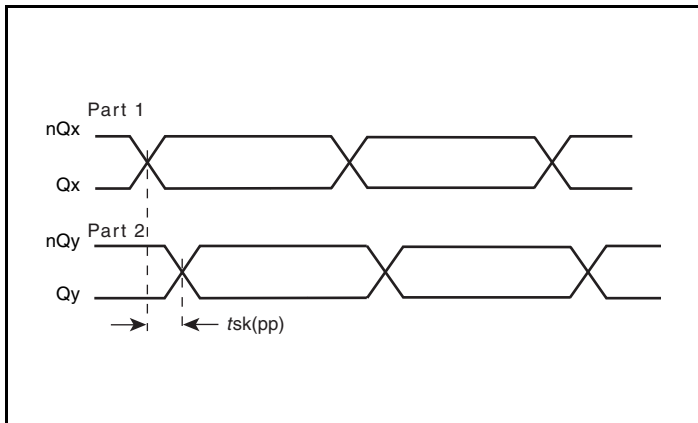
Parameter Measurement Information



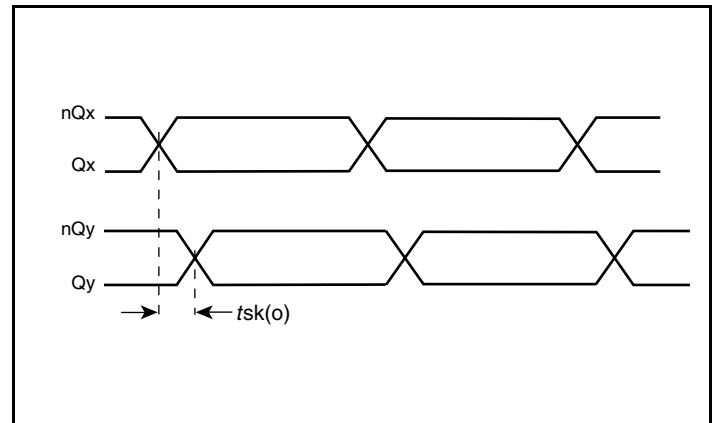
LVDS Output Load AC Test Circuit



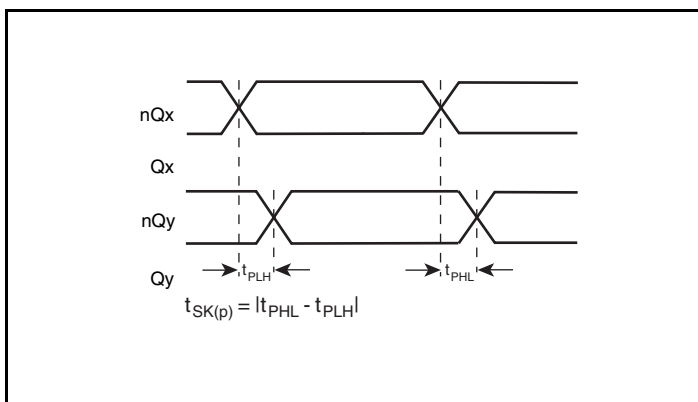
Differential Input Level



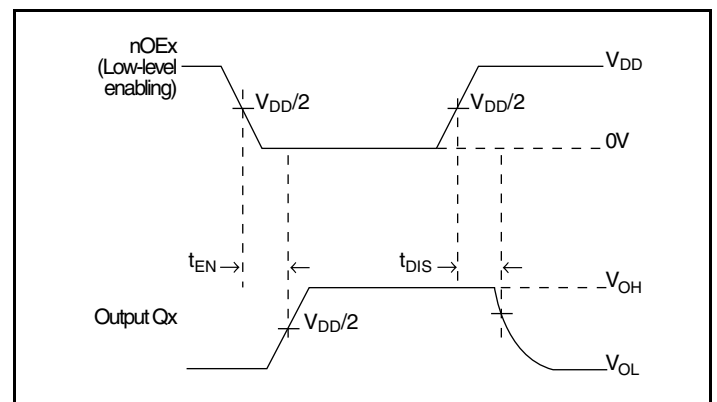
Part-to-Part Skew



Output Skew

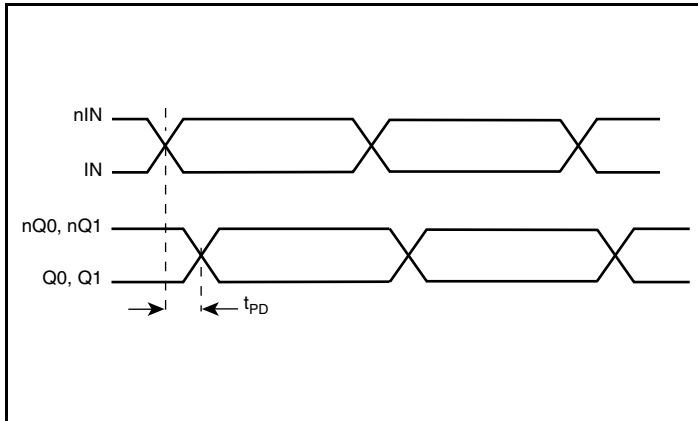


Output Pulse Skew

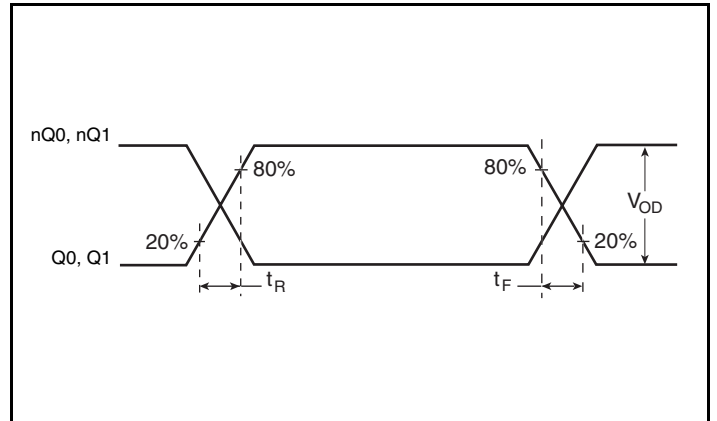


Output Enable/Disable Time

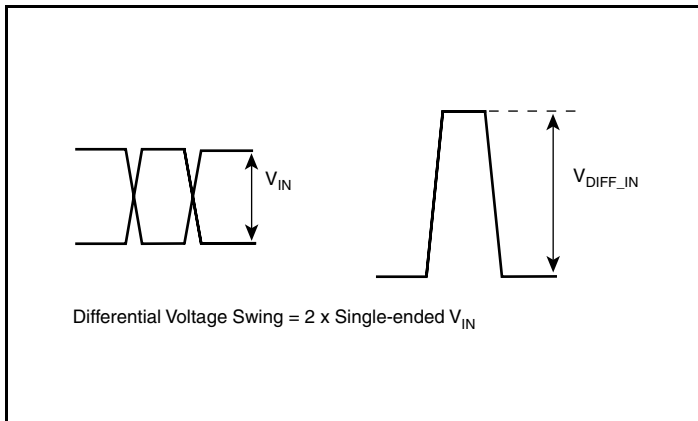
Parameter Measurement Information, continued



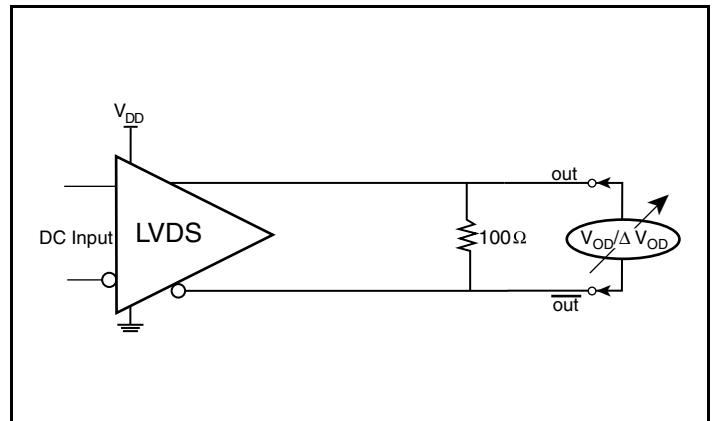
Propagation Delay



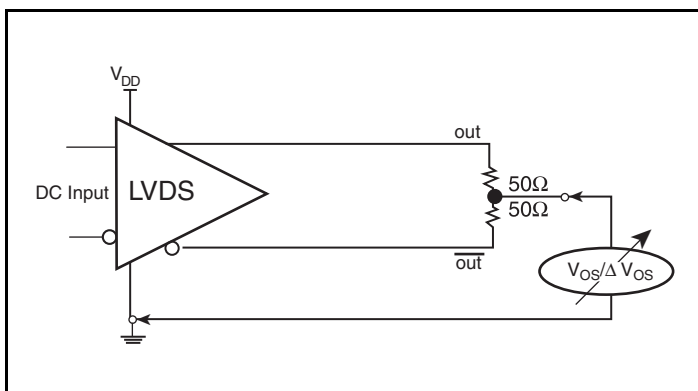
Output Rise/Fall Time



Single-Ended & Differential Input Voltage Swing

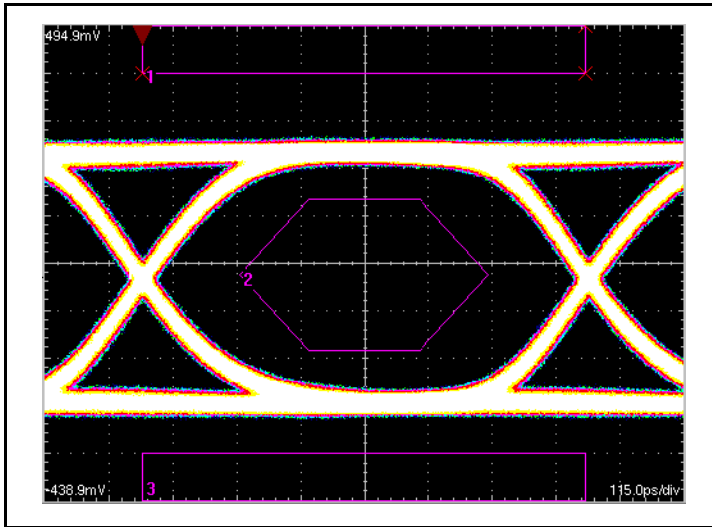


Differential Output Voltage Setup

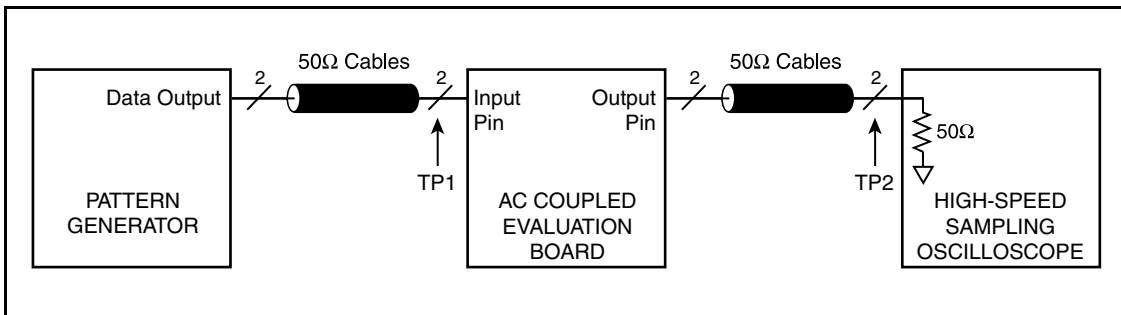


Offset Voltage Setup

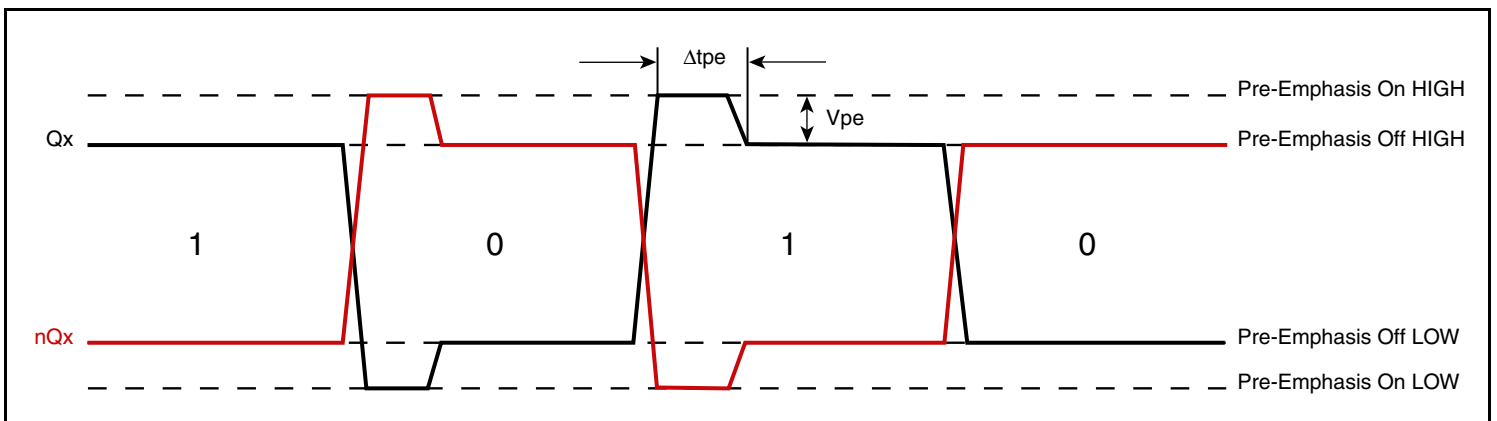
Parameter Measurement Information, continued



1.2GHz NRZ (PRBS Pattern) GbE Mask, Pre-Emphasis On



Deterministic Jitter and Total Jitter (peak-to-peak)



Output Pre-Emphasis Voltage Ratio & Duration

Applications Information

Differential Input with Built-in 50Ω Termination Interface

The IN/nIN with built-in 50Ω terminations accepts LVDS, LVPECL, CML and other differential signals. Both signals must meet the V_{PP} and V_{CMR} input requirements. *Figures 1A to 1E* show interface examples for the IN/nIN input with built-in 50Ω terminations driven by

the most common driver types. The input interfaces suggested here are examples only. If the driver is from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements.

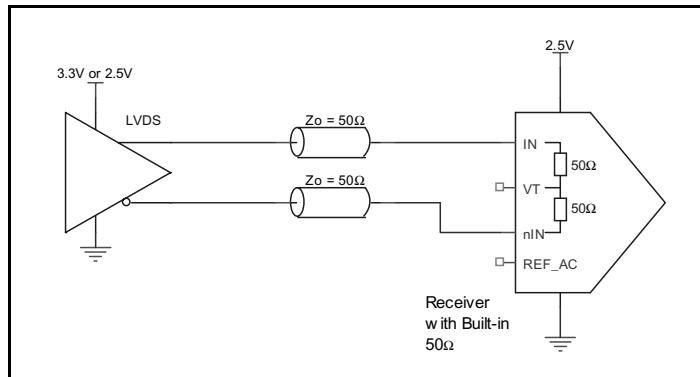


Figure 1A. IN/nIN Input with Built-In 50Ω Driven by an LVDS Driver

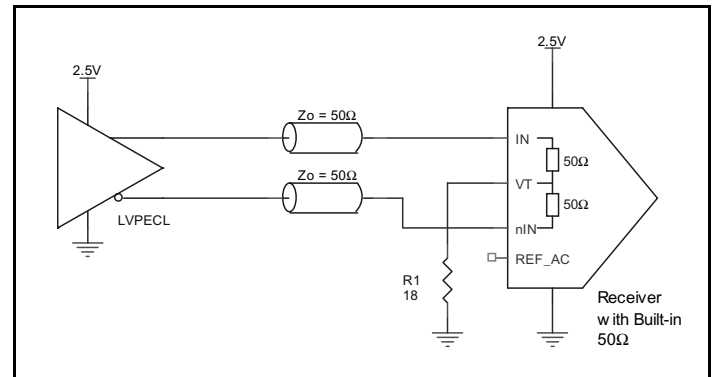


Figure 1B. IN/nIN Input with Built-In 50Ω Driven by an LVPECL Driver

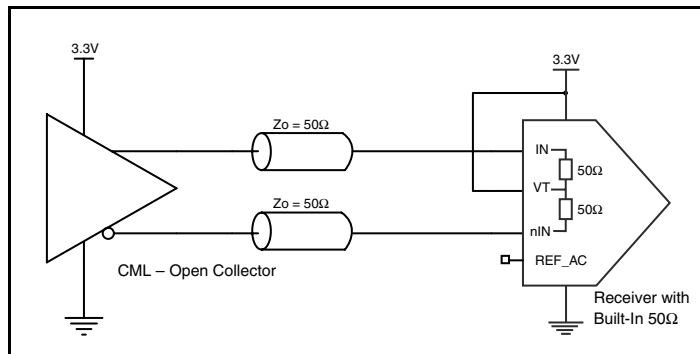


Figure 1C. IN/nIN Input with Built-In 50Ω Driven by a CML Driver

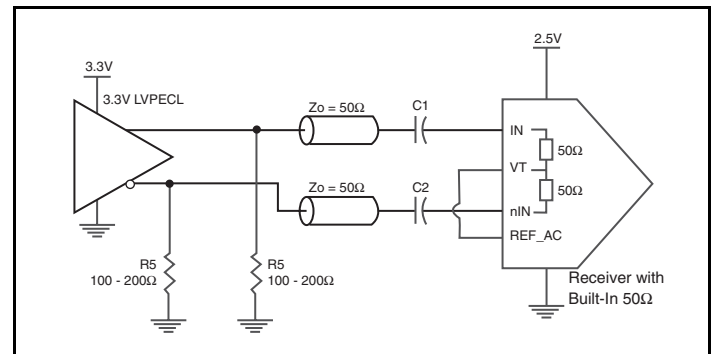


Figure 1D. IN/nIN Input with Built-In 50Ω Driven by an LVPECL Driver

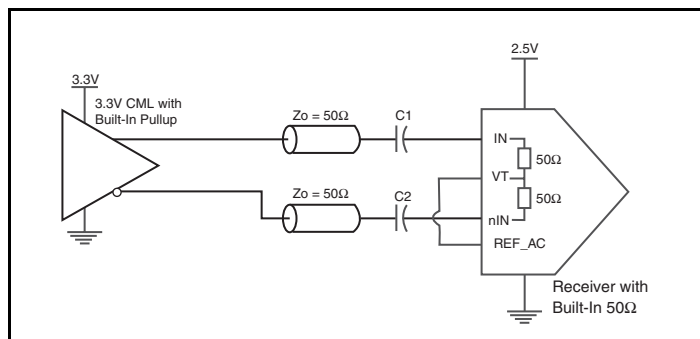


Figure 1E. IN/nIN Input with Built-In 50Ω Driven by a 3.3V CML Driver with Built-In Pullup

Recommendations for Unused Input and Output Pins

Inputs:

LVC MOS Select Pins

All control pins have internal pulldowns; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

Outputs:

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100 Ω across. If they are left floating, we recommend that there is no trace attached.

LVDS Driver Termination

A general LVDS interface is shown in *Figure 2*. Standard termination for LVDS type output structure requires both a 100 Ω parallel resistor at the receiver and a 100 Ω differential transmission line environment. In order to avoid any transmission line reflection issues, the 100 Ω resistor must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The standard

termination schematic as shown in Figure 2 can be used with either type of output structure. If using a non-standard termination, it is recommended to contact IDT and confirm if the output is a current source or a voltage source type structure. In addition, since these outputs are LVDS compatible, the amplitude and common mode input range of the input receivers should be verified for compatibility with the output.

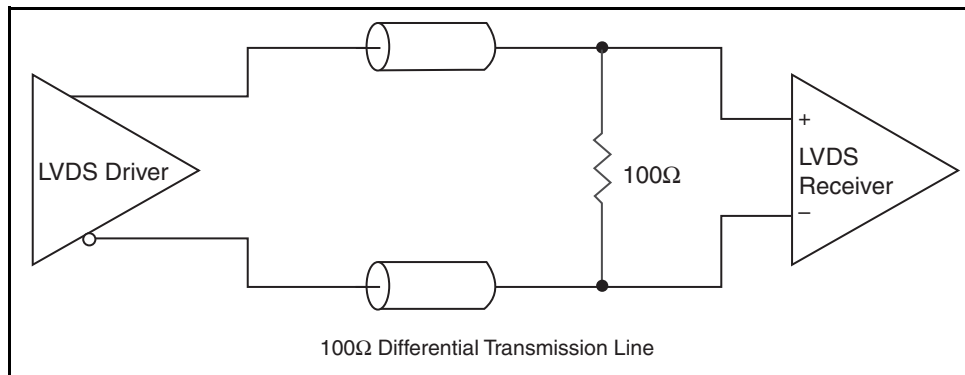


Figure 2. Typical LVDS Driver Termination

VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 3*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor's Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.

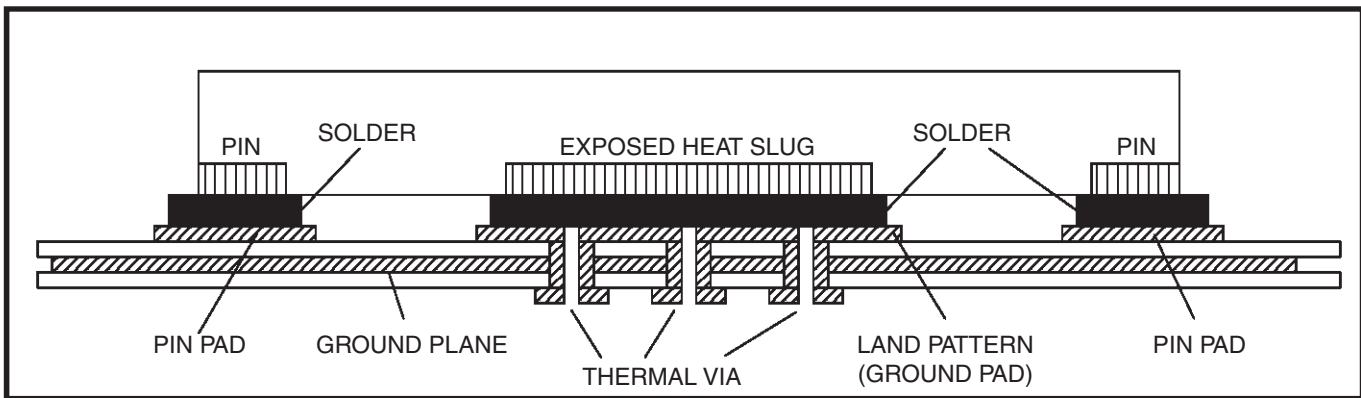


Figure 3. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)

Power Considerations

This section provides information on power dissipation and junction temperature for the ICS854S712I. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS854S712I is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{DD_MAX} * I_{DD_MAX} = 3.465V * 90mA = \mathbf{311.85mW}$
- Power Dissipation for internal termination R_T
Power (R_T)_{MAX} = $(V_{IN_MAX})^2 / R_{T_MIN} = (1.2V)^2 / 80\Omega = \mathbf{18mW}$

Total Power_{MAX} = 311.85mW + 18mW = **329.85mW**

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 74.7°C/W per Table 6 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.330\text{W} * 74.7^\circ\text{C/W} = 109.7^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 6. Thermal Resistance θ_{JA} for 16 Lead VFQFN, Forced Convection

θ_{JA} by Velocity			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	74.7°C/W	65.3°C/W	58.5°C/W

Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 16 Lead VFQFN

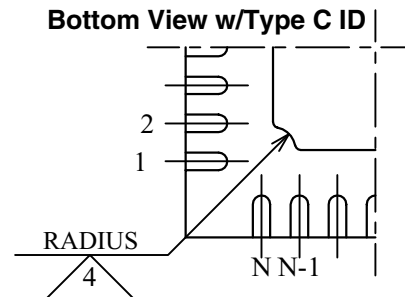
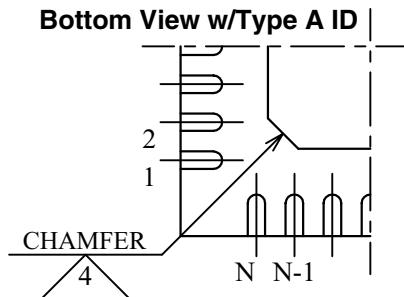
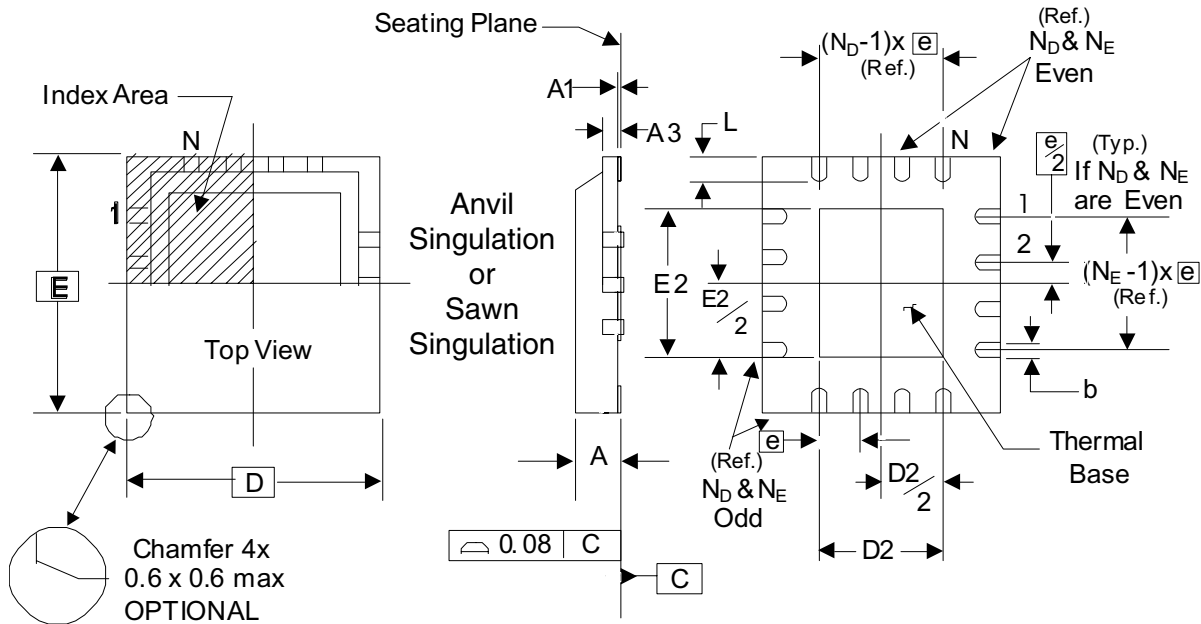
θ_{JA} by Velocity			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	74.7°C/W	65.3°C/W	58.5°C/W

Transistor Count

The transistor count for ICS854S712I is: 439

Package Outline and Package Dimensions

Package Outline - K Suffix for 16 Lead VFQFN



There are 2 methods of indicating pin 1 corner at the back of the VFQFN package are:

1. Type A: Chamfer on the paddle (near pin 1)
2. Type C: Mouse bite on the paddle (near pin 1)

Table 8. Package Dimensions

JEDEC Variation: VEED-2/-4 All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	16	
A	0.80	1.00
A1	0	0.05
A3	0.25 Ref.	
b	0.18	0.30
$N_D \& N_E$	4	
D & E	3.00 Basic	
D2 & E2	1.00	1.80
e	0.50 Basic	
L	0.30	0.50

Reference Document: JEDEC Publication 95, MO-220

Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
854S712AKILF	2AIL	"Lead-Free" 16 Lead VFQFN	Tray	-40°C to 85°C
854S712AKILFT	2AIL	"Lead-Free" 16 Lead VFQFN	2500 Tape & Reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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